

IRF7343

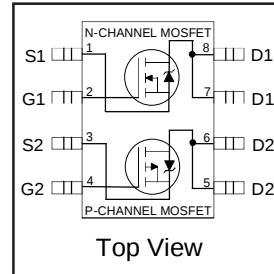
HEXFET® Power MOSFET

- Generation V Technology
- Ultra Low On-Resistance
- Dual N and P Channel MOSFET
- Surface Mount
- Fully Avalanche Rated

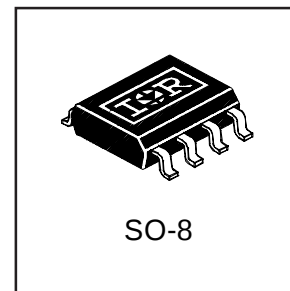
Description

Fifth Generation HEXFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET Power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

The SO-8 has been modified through a customized leadframe for enhanced thermal characteristics and multiple-die capability making it ideal in a variety of power applications. With these improvements, multiple devices can be used in an application with dramatically reduced board space. The package is designed for vapor phase, infra red, or wave soldering techniques.



	N-Ch	P-Ch
V_{DS}	55V	-55V
$R_{DS(on)}$	0.050Ω	0.105Ω



SO-8

Absolute Maximum Ratings

	Parameter	Max.		Units
		N-Channel	P-Channel	
V_{DS}	Drain-Source Voltage	55	-55	V
$I_D @ T_A = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	4.7	-3.4	A
$I_D @ T_A = 70^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	3.8	-2.7	
I_{DM}	Pulsed Drain Current ①	38	-27	
$P_D @ T_A = 25^\circ\text{C}$	Maximum Power Dissipation ⑤	2.0		W
$P_D @ T_A = 70^\circ\text{C}$	Maximum Power Dissipation ⑤	1.3		W
E_{AS}	Single Pulse Avalanche Energy③	72	114	mJ
I_{AR}	Avalanche Current	4.7	-3.4	A
E_{AR}	Repetitive Avalanche Energy	0.20		mJ
V_{GS}	Gate-to-Source Voltage	± 20		V
dv/dt	Peak Diode Recovery dv/dt ②	5.0	-5.0	V/ns
T_J, T_{STG}	Junction and Storage Temperature Range	-55 to + 150		°C

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JA}$	Maximum Junction-to-Ambient ⑤	—	62.5	°C/W

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

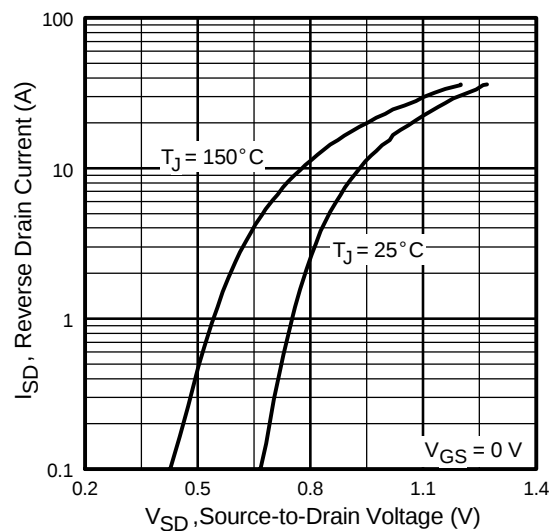
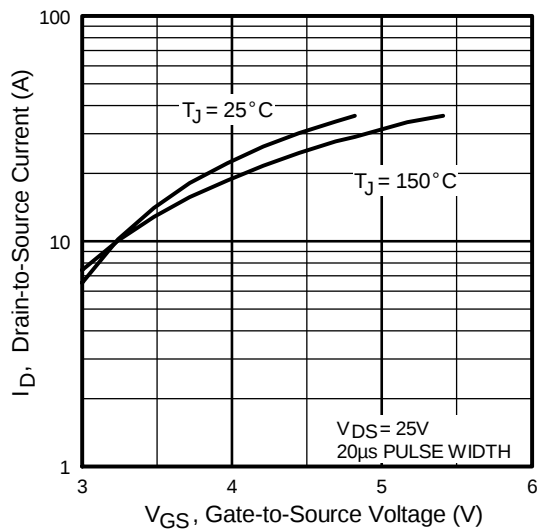
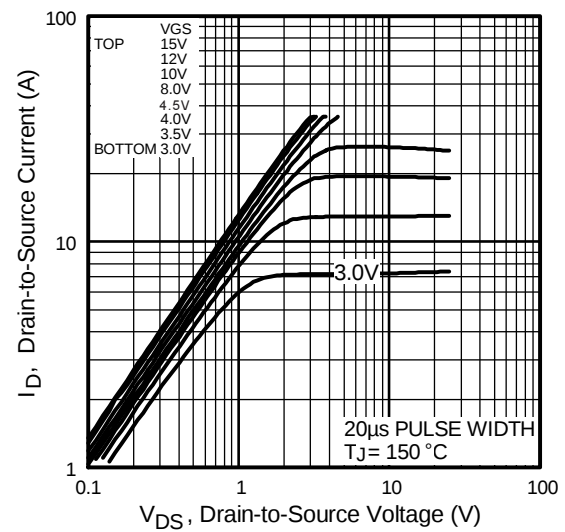
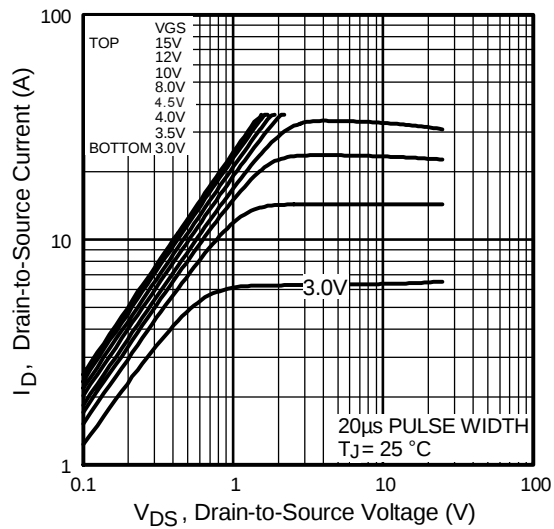
	Parameter		Min.	Typ.	Max.	Units	Conditions
V _{(BR)DSS}	Drain-to-Source Breakdown Voltage	N-Ch	55	—	—	V	V _{GS} = 0V, I _D = 250μA
		P-Ch	-55	—	—		V _{GS} = 0V, I _D = -250μA
ΔV _{(BR)DSS} /ΔT _J	Breakdown Voltage Temp. Coefficient	N-Ch	—	0.059	—	V/°C	Reference to 25°C, I _D = 1mA
		P-Ch	—	0.054	—		Reference to 25°C, I _D = -1mA
R _{DS(ON)}	Static Drain-to-Source On-Resistance	N-Ch	—	0.043	0.050	Ω	V _{GS} = 10V, I _D = 4.7A ④
			—	0.056	0.065		V _{GS} = 4.5V, I _D = 3.8A ④
		P-Ch	—	0.095	0.105		V _{GS} = -10V, I _D = -3.4A ④
			—	0.150	0.170		V _{GS} = -4.5V, I _D = -2.7A ④
V _{GS(th)}	Gate Threshold Voltage	N-Ch	1.0	—	—	V	V _{DS} = V _{GS} , I _D = 250μA
		P-Ch	-1.0	—	—		V _{DS} = V _{GS} , I _D = -250μA
g _{fs}	Forward Transconductance	N-Ch	7.9	—	—	S	V _{DS} = 10V, I _D = 4.5A ④
		P-Ch	3.3	—	—		V _{DS} = -10V, I _D = -3.1A ④
I _{DSS}	Drain-to-Source Leakage Current	N-Ch	—	—	2.0	μA	V _{DS} = 55V, V _{GS} = 0V
		P-Ch	—	—	-2.0		V _{DS} = -55V, V _{GS} = 0V
		N-Ch	—	—	25		V _{DS} = 55V, V _{GS} = 0V, T _J = 55°C
		P-Ch	—	—	-25		V _{DS} = -55V, V _{GS} = 0V, T _J = 55°C
I _{GSS}	Gate-to-Source Forward Leakage	N-P	—	—	±100	nA	V _{GS} = ±20V
Q _g	Total Gate Charge	N-Ch	—	24	36	nC	N-Channel
		P-Ch	—	26	38		I _D = 4.5A, V _{DS} = 44V, V _{GS} = 10V ④
Q _{gs}	Gate-to-Source Charge	N-Ch	—	2.3	3.4		
		P-Ch	—	3.0	4.5		
Q _{gd}	Gate-to-Drain ("Miller") Charge	N-Ch	—	7.0	10		P-Channel
		P-Ch	—	8.4	13		I _D = -3.1A, V _{DS} = -44V, V _{GS} = -10V ④
t _{d(on)}	Turn-On Delay Time	N-Ch	—	8.3	12	ns	N-Channel
		P-Ch	—	14	22		V _{DD} = 28V, I _D = 1.0A, R _G = 6.0Ω, R _D = 28Ω ④
t _r	Rise Time	N-Ch	—	3.2	4.8		
		P-Ch	—	10	15		
t _{d(off)}	Turn-Off Delay Time	N-Ch	—	32	48		P-Channel
		P-Ch	—	43	64		V _{DD} = -28V, I _D = -1.0A, R _G = 6.0Ω, R _D = 28Ω ④
t _f	Fall Time	N-Ch	—	13	20		
		P-Ch	—	22	32		
C _{iss}	Input Capacitance	N-Ch	—	740	—	pF	N-Channel
		P-Ch	—	690	—		V _{GS} = 0V, V _{DS} = 25V, f = 1.0MHz
C _{oss}	Output Capacitance	N-Ch	—	190	—		P-Channel
		P-Ch	—	210	—		V _{GS} = 0V, V _{DS} = -25V, f = 1.0MHz
C _{rss}	Reverse Transfer Capacitance	N-Ch	—	71	—		
		P-Ch	—	86	—		

Source-Drain Ratings and Characteristics

	Parameter		Min.	Typ.	Max.	Units	Conditions
I _S	Continuous Source Current (Body Diode)	N-Ch	—	—	2.0	A	
		P-Ch	—	—	-2.0		
I _{SM}	Pulsed Source Current (Body Diode) ①	N-Ch	—	—	38		
		P-Ch	—	—	-27		
V _{SD}	Diode Forward Voltage	N-Ch	—	0.70	1.2	V	T _J = 25°C, I _S = 2.0A, V _{GS} = 0V ③
		P-Ch	—	-0.80	-1.2		T _J = 25°C, I _S = -2.0A, V _{GS} = 0V ③
t _{rr}	Reverse Recovery Time	N-Ch	—	60	90	ns	N-Channel
		P-Ch	—	54	80		T _J = 25°C, I _F = 2.0A, di/dt = 100A/μs ④
Q _{rr}	Reverse Recovery Charge	N-Ch	—	120	170	nC	P-Channel
		P-Ch	—	85	130		T _J = 25°C, I _F = -2.0A, di/dt = 100A/μs ④

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 22)
- ② N-Channel I_{SD} ≤ 4.7A, di/dt ≤ 220A/μs, V_{DD} ≤ V_{(BR)DSS}, T_J ≤ 150°C
P-Channel I_{SD} ≤ -3.4A, di/dt ≤ -150A/μs, V_{DD} ≤ V_{(BR)DSS}, T_J ≤ 150°C
- ③ N-Channel Starting T_J = 25°C, L = 6.5mH R_G = 25Ω, I_{AS} = 4.7A.
P-Channel Starting T_J = 25°C, L = 20mH R_G = 25Ω, I_{AS} = -3.4A.
- ④ Pulse width ≤ 300μs; duty cycle ≤ 2%.
- ⑤ Surface mounted on FR-4 board, t ≤ 10sec.



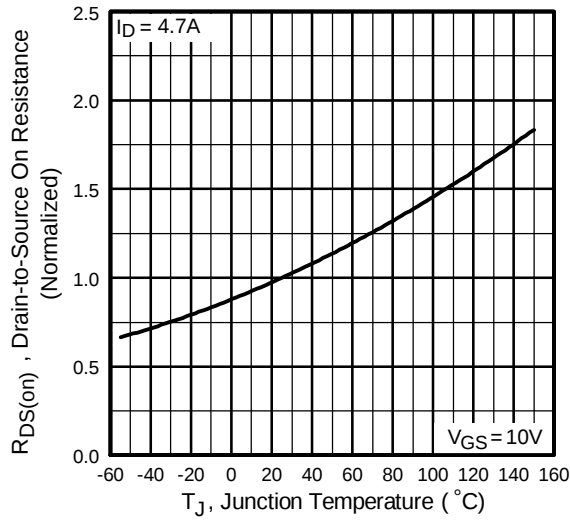


Fig 5. Normalized On-Resistance Vs. Temperature

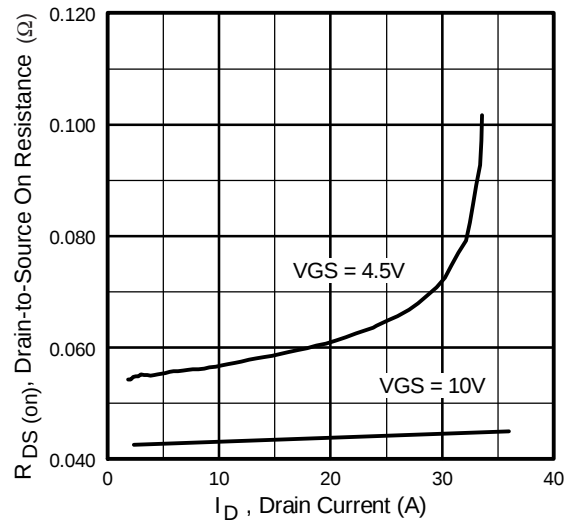


Fig 6. Typical On-Resistance Vs. Drain Current

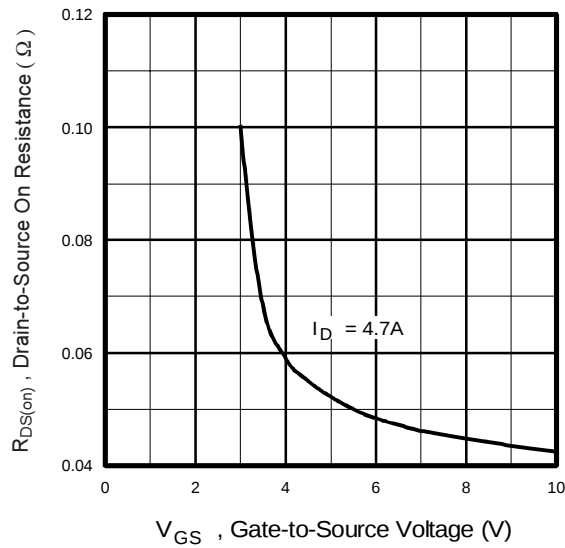


Fig 7. Typical On-Resistance Vs. Gate Voltage

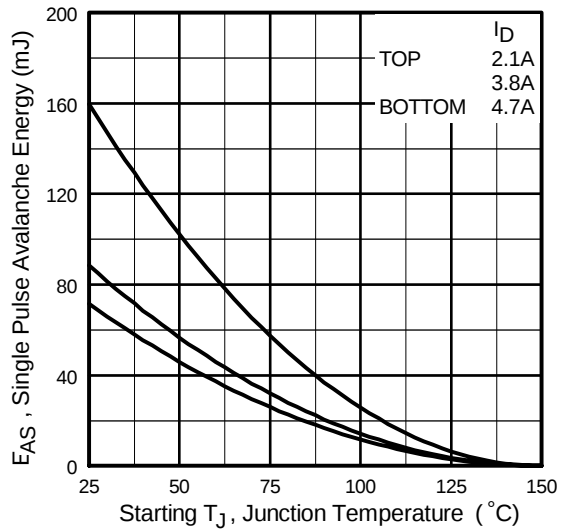
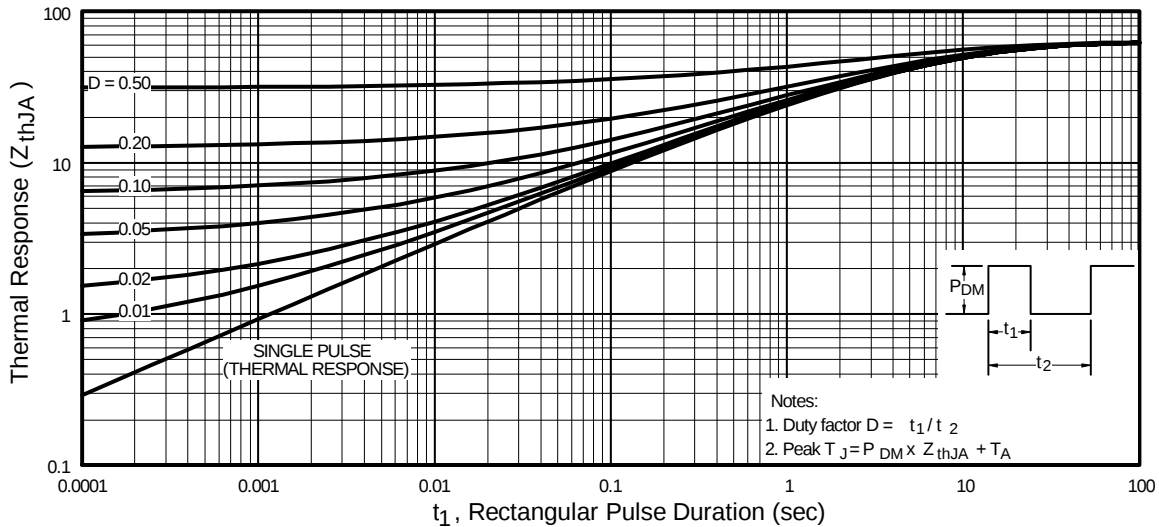
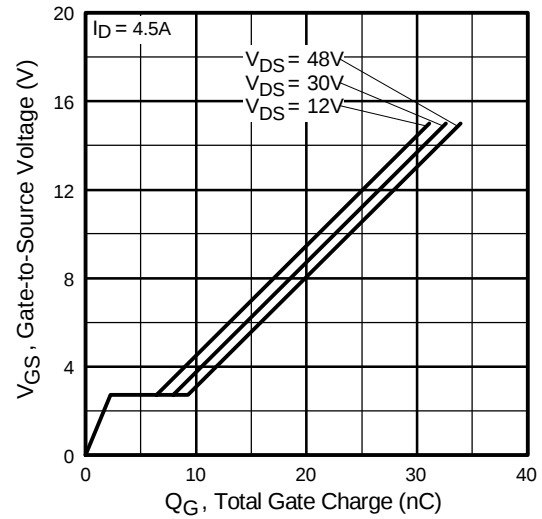
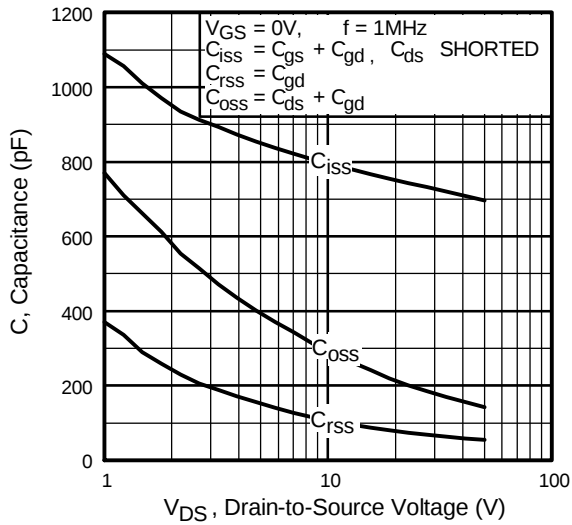


Fig 8. Maximum Avalanche Energy Vs. Drain Current



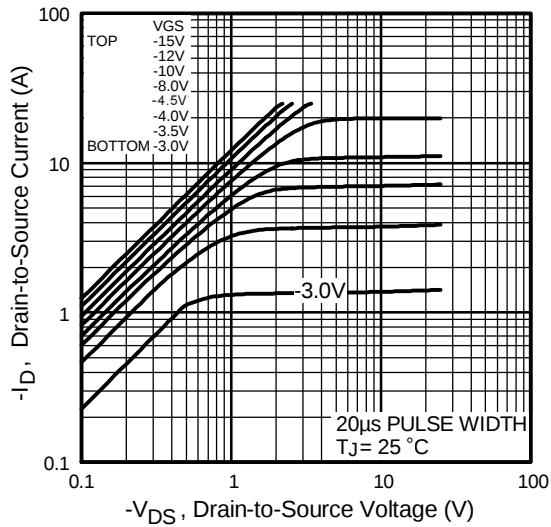


Fig 12. Typical Output Characteristics

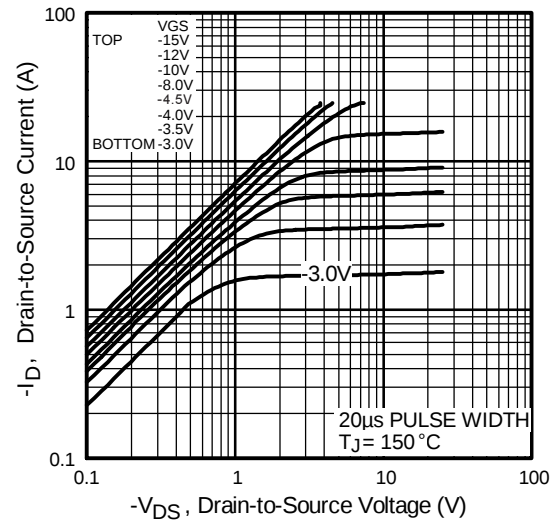


Fig 13. Typical Output Characteristics

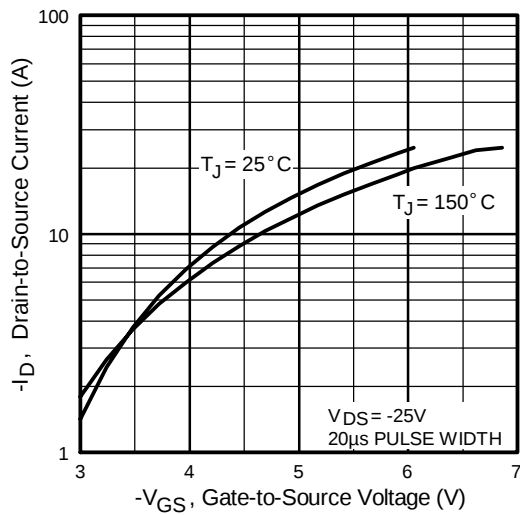


Fig 14. Typical Transfer Characteristics

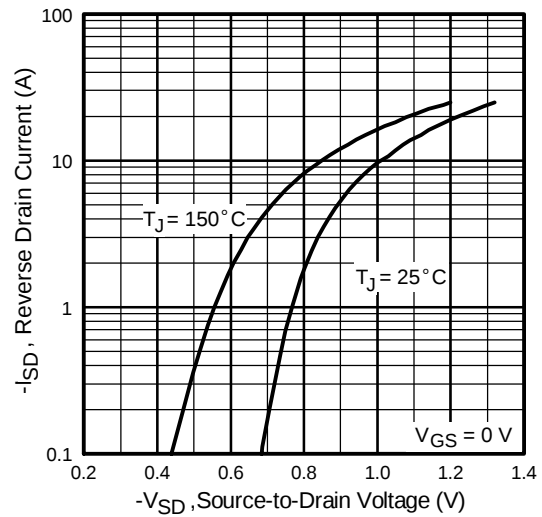


Fig 15. Typical Source-Drain Diode Forward Voltage

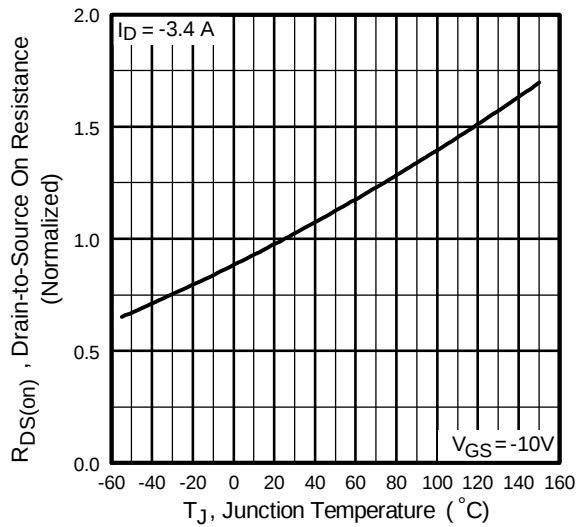


Fig 16. Normalized On-Resistance Vs. Temperature

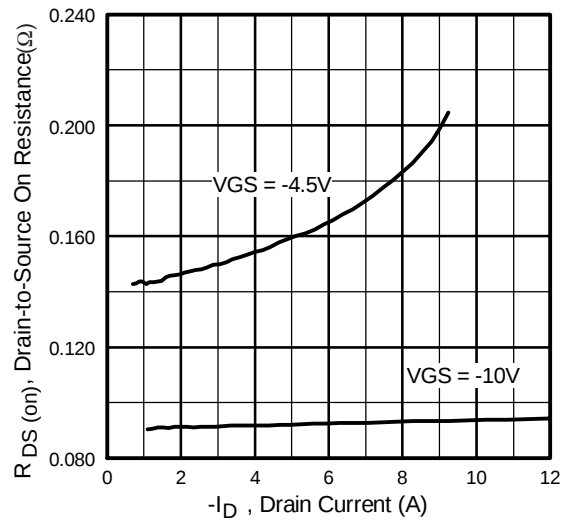


Fig 17. Typical On-Resistance Vs. Drain Current

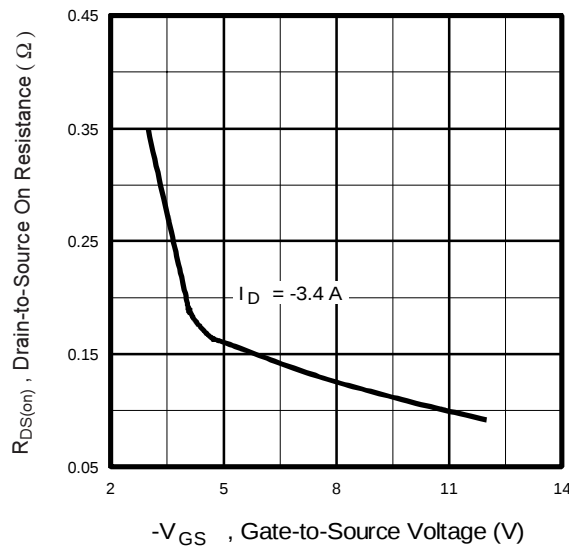


Fig 18. Typical On-Resistance Vs. Gate Voltage

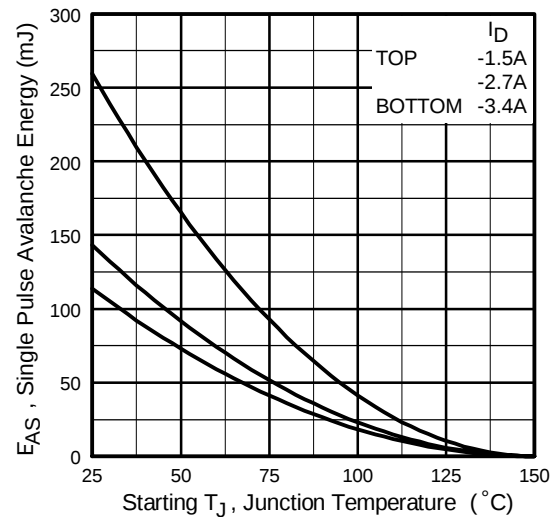
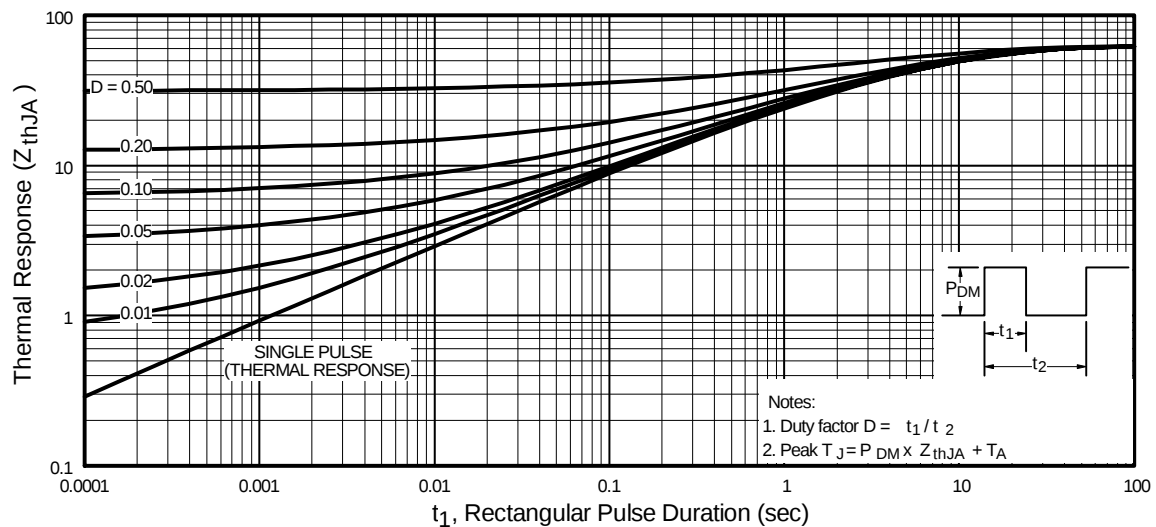
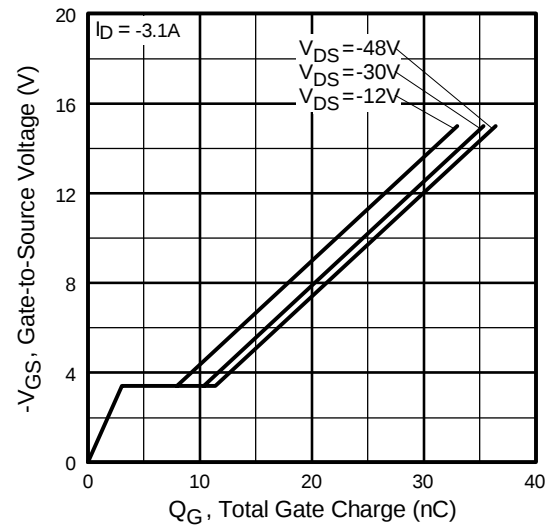
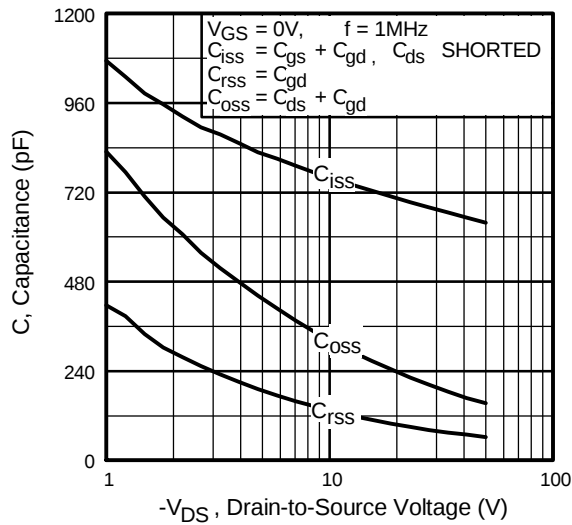
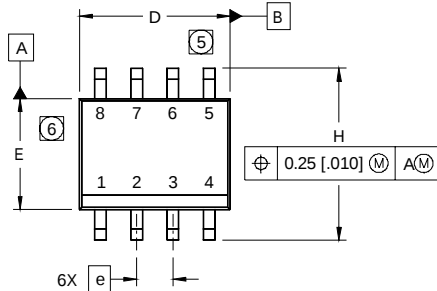


Fig 19. Maximum Avalanche Energy Vs. Drain Current

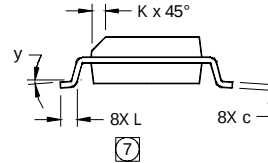
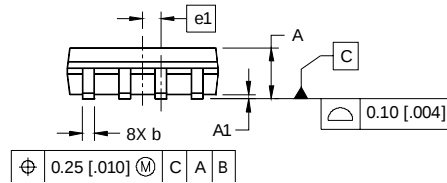


SO-8 Package Outline

Dimensions are shown in millimeters (inches)



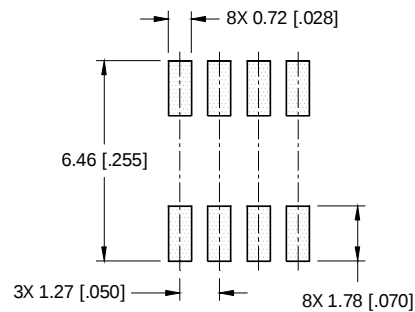
DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.0532	.0688	1.35	1.75
A1	.0040	.0098	0.10	0.25
b	.013	.020	0.33	0.51
c	.0075	.0098	0.19	0.25
D	.189	.1968	4.80	5.00
E	.1497	.1574	3.80	4.00
e	.050 BASIC		1.27 BASIC	
e1	.025 BASIC		0.635 BASIC	
H	.2284	.2440	5.80	6.20
K	.0099	.0196	0.25	0.50
L	.016	.050	0.40	1.27
y	0°	8°	0°	8°



NOTES:

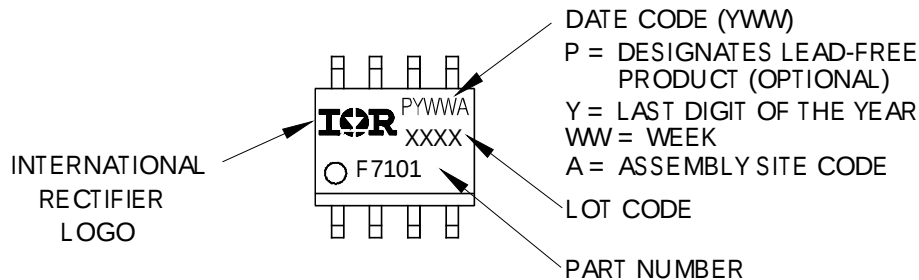
1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
2. CONTROLLING DIMENSION: MILLIMETER
3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.
5. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.15 [0.006].
6. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.25 [0.010].
7. DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE.

FOOTPRINT



SO-8 Part Marking

EXAMPLE: THIS IS AN IRF7101 (MOSFET)

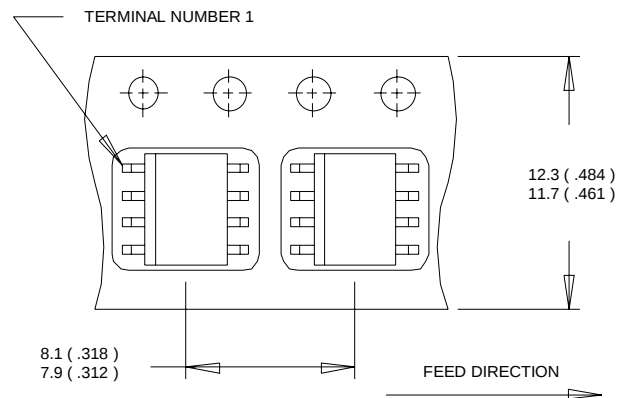


IRF7343

International
IR Rectifier

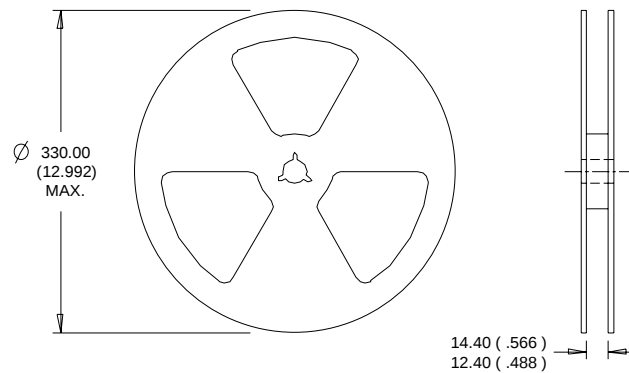
SO-8 Tape and Reel

Dimensions are shown in millimeters (inches)



NOTES:

1. CONTROLLING DIMENSION : MILLIMETER.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).
3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



NOTES :

1. CONTROLLING DIMENSION : MILLIMETER.
2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

Data and specifications subject to change without notice.

International
IR Rectifier

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TAC Fax: (310) 252-7903

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